

Silicon NPN Power Transistors

2SC3795 2SC3795A

DESCRIPTION

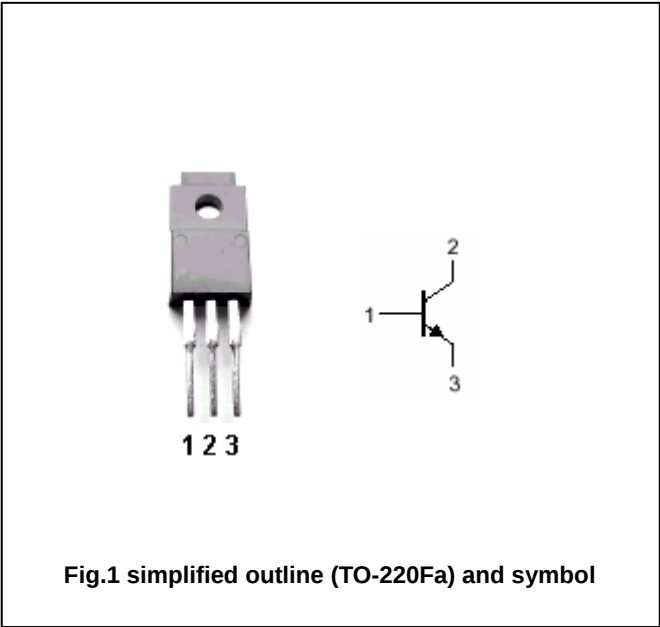
- With TO-220Fa package
- High breakdown voltage
- High speed switching
- Low collector saturation voltage

APPLICATIONS

- For high breakdown voltate ,high-speed switching applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



Absolute maximum ratings (Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	2SC3795	800	V
		2SC3795A	900	
V _{CEO}	Collector-emitter voltage	Open base	500	V
V _{EBO}	Emitter-base voltage	Open collector	8	V
I _C	Collector current (DC)		5	A
I _{CM}	Collector current-Peak		10	A
I _B	Base current		3	A
P _C	Collector power dissipation	T _C =25	40	W
		T _a =25	2	
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

Tj=25 unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEQ(SUS)}$	Collector-emitter sustaining voltage		$I_C=0.2A$, $L=25mH$	500			V
V_{CEsat}	Collector-emitter saturation voltage		$I_C=3A$; $I_B=0.6A$			1.0	V
V_{BEsat}	Base-emitter saturation voltage		$I_C=3A$; $I_B=0.6A$			1.5	V
I_{CBO}	Collector cut-off current	2SC3795	$V_{CB}=800V$; $I_E=0$			0.1	mA
		2SC3795A	$V_{CB}=900V$; $I_E=0$				
I_{EBO}	Emitter cut-off current		$V_{EB}=5V$; $I_C=0$			0.1	mA
h_{FE-1}	DC current gain		$I_C=0.1A$; $V_{CE}=5V$	15			
h_{FE-2}	DC current gain		$I_C=3A$; $V_{CE}=5V$	8			
f_T	Transition frequency		$I_C=0.5A$; $V_{CE}=10V$		8		MHz

Switching times

t_{on}	Turn-on time	2SC3795	$I_C=3A$; $I_{B1}=-I_{B2}=0.6A$ $V_{CC}=200V$			1.0	μs
		2SC3795A				1.2	
t_s	Storage time					3.0	μs
t_f	Fall time	2SC3795				1.0	μs
		2SC3795A				1.2	

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PACKAGE OUTLINE

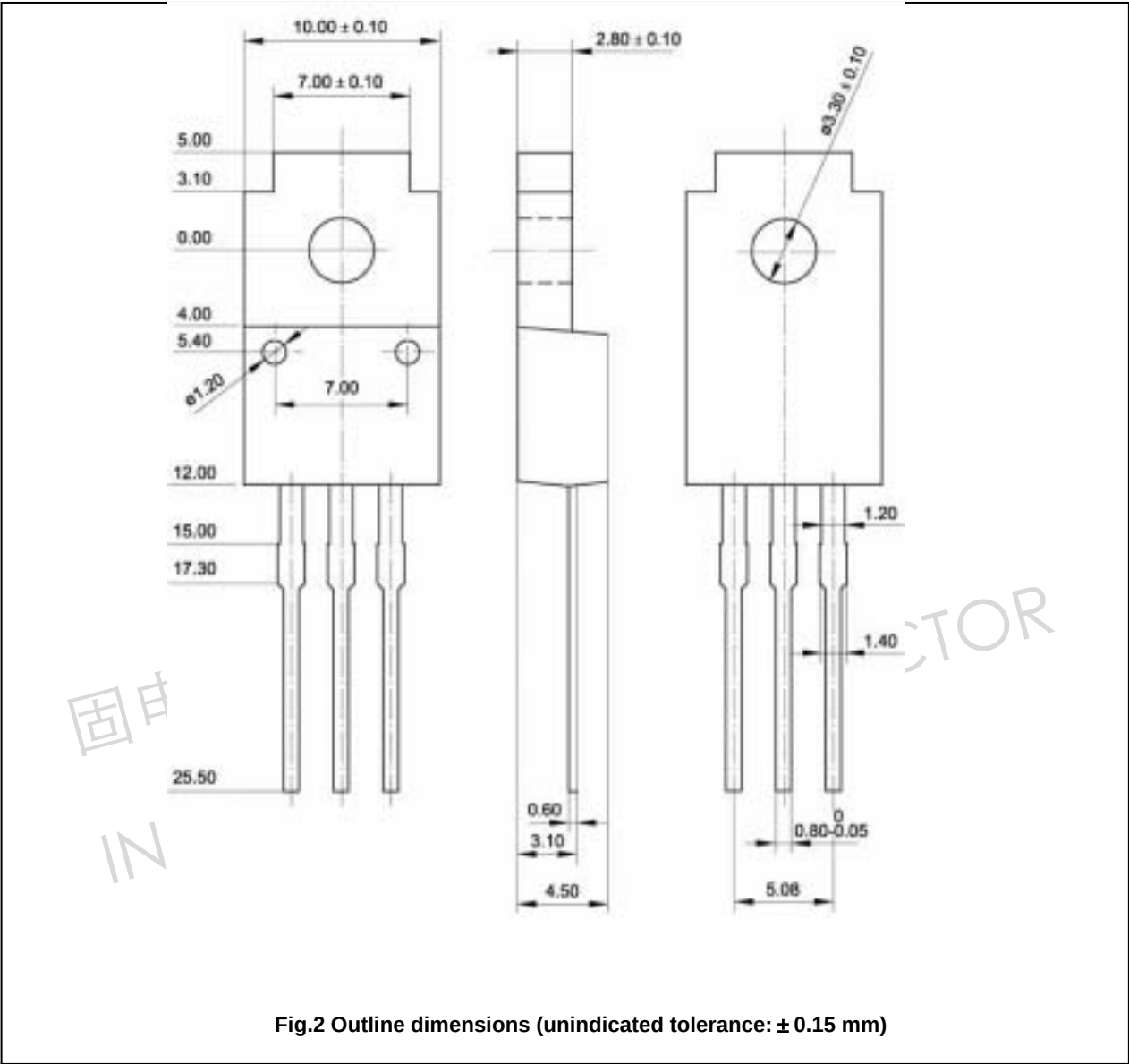


Fig.2 Outline dimensions (unindicated tolerance: ± 0.15 mm)

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